## NSN 5961-01-364-1227

Diode Semiconductor Device - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-01-364-1227 **Inclosure Material:** Glass **Overall Length:** 0.170 inches **Overall Diameter:** 0.076 inches **Mounting Method: Terminal Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 100.0 nonrepetitive peak reverse voltage **Current Rating Per Characteristic:** 1.00 microamperes forward current, average peak **Power Rating Per Characteristic:** 250.0 milliwatts small-signal input power, common-collector preset **Capacitance Rating In Picofarads:** 0.4 **Maximum Operating Tempurature Per Measurement Point:** 150.0 degrees celsius junction **Test Data Document:** 87990-755002a7702 drawing (this is the basic governing drawing, such as a contractor drawing, original equipment manufacturer drawing, etc.; excludes any specification, standard or other document that may be referenced in a basic governing drawing) **Terminal Type And Quantity:** 2 uninsulated wire lead Shelf Life: N/a **Unit Of Measure: Demilitarization:** No Fiig: A110a0